

ACPM-7357

UMTS Dual-Band 4x5mm Power Amplifier Module (Band1/Band8)



Data Sheet

Description

The ACPM-7357 is a dual-band PAM (Power Amplifier Module) designed for UMTS Band1 and Band8. The ACPM-7357 meets stringent UMTS linearity requirements. The 4mmx5mm form factor 14-pin surface mount package is self contained, incorporating 50ohm input and output matching networks

The ACPM-7357 features 5th generation of CoolPAM circuit technology which supports 3 modes – bypass, mid and high power modes. The CoolPAM is stage bypass technology which enables power amplifier to lower power consumption. Active bypass feature is added to 5th generation to enhance power added efficiency at low output range and this technology extends talk time of mobiles more by further saving power amplifier’s current consumption.

The power amplifier is manufactured on an advanced InGaP HBT (hetero-junction Bipolar Transistor) MMIC (microwave monolithic integrated circuit) technology offering state-of-the-art reliability, temperature stability and ruggedness

The Module is housed in a cost effective, small and thin 4x5mm package.

Features

- Dual-Band PA (Band1 and Band8)
- Small Size (4x5mm)
- Thin Package (1.0mm typ)
- Excellent Linearity
- 3-mode power control
Bypass / Mid Power Mode / High Power Mode
- High Efficiency at max output power
- 14-pin surface mounting package
- Internal 50ohm matching networks for both RF input and output
- Lead-free, RoHS compliant, Green

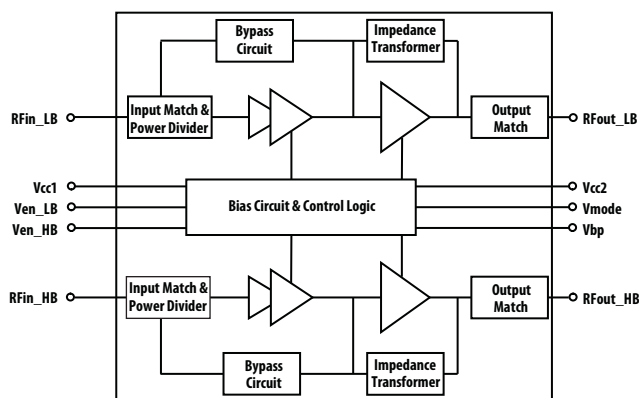
Applications

- UMTS Band1 and Band8

Ordering Information

| Part Number | Number of Devices | Container |
|---------------|-------------------|----------------------|
| ACPM-7357-TR1 | 1000 | 178mm (7") Tape/Reel |
| ACPM-7357-BLK | 100 | Bulk |

Block Diagram



Absolute Maximum Ratings

No damage assuming only one parameter is set at limit at a time with all other parameters set at or below typical value.

Operation of any single parameter outside these conditions with the remaining parameters set at or below typical values may result in permanent damage

| Description | Min | Typ | Max | Unit | Associated Pins |
|----------------------------------|-----|-----|------|------|---------------------|
| RF Input Power (high power mode) | | 0 | 10 | dBm | RFin_Hi, RFin_Low |
| Output power (bypass mode) | | | 10 | | RFOut_Hi, RFOut_Low |
| Output power (mid power mode) | | | 18 | | RFOut_Hi, RFOut_Low |
| DC Supply Voltage | 0 | 3.4 | 5.0 | V | Vcc1, Vcc2 |
| Enable Voltage | 0 | 2.6 | 3.3 | V | Ven_Low, Ven_Hi |
| Mode Control Voltage | 0 | 2.6 | 3.3 | V | Vmode |
| Bypass Control | 0 | 2.6 | 3.3 | V | Vbp |
| Storage Temperature | -55 | 25 | +125 | °C | |

Recommended Operating Condition

| Description | | Min | Typ | Max | Unit |
|-------------------------------------|------|------|-----|------|------|
| DC Supply Voltage | | 3.2 | 3.4 | 4.2 | V |
| Enable Voltage (Ven_Low, Ven_Hi) | LOW | 0 | 0 | 0.5 | V |
| | HIGH | 1.35 | 2.6 | 3.1 | V |
| Mode Control Voltage (Vmode) | LOW | 0 | 0 | 0.5 | V |
| | HIGH | 1.35 | 2.6 | 3.1 | V |
| Bypass Control Voltage (Vbp) | LOW | 0 | 0 | 0.5 | V |
| | HIGH | 1.35 | 2.6 | 3.1 | V |
| Operating Frequency Band8 | | 890 | | 915 | MHz |
| Band1 | | 1920 | | 1980 | MHz |
| Ambient Temperature | | -30 | 25 | 85 | °C |

Operating Logic Table

| Power Mode | Ven_Low, Ven_Hi | Vbp | Vmode | Pout (Rel99) | Pout (HSDPA, HSUPA MPR=0dB) |
|-----------------|--------------------|------|-------|-------------------------------------|---------------------------------------|
| High Power Mode | HIGH | LOW | LOW | ~27.0dBm (Band1) ~27.5dBm(Band8) | ~26.0dBm (Band1) ~ 26.5dBm (Band8) |
| Mid Power Mode | HIGH | LOW | HIGH | ~17dBm | ~16dBm |
| Bypass Mode | HIGH | HIGH | HIGH | ~8dBm | ~7dBm |
| Shut Down Mode | LOW | LOW | LOW | - | - |

Electrical Characteristics in Band1

– Conditions: Vcc=3.4V, Ven_Hi=2.6V, T=25°C, Zin/Zout=50ohm

– Signal Configuration: 3GPP (DPCCH+1DPDCH) Up-Link unless specified otherwise

| Characteristics | Condition | Min | Typ | Max | Unit |
|----------------------------------|---|---|------|-------|--------|
| Operating Frequency Range | | 1920 | – | 1980 | MHz |
| Gain | High Power Mode, Pout=27dBm | 24 | 27.3 | | dB |
| | Mid Power Mode, Pout=17dBm | 15 | 20.8 | | dB |
| | Bypass Power Mode, Pout=8dBm | 10 | 14.0 | | dB |
| Total Supply Current | High Power Mode, Pout=27dBm | | 400 | 450 | mA |
| | Mid Power Mode, Pout=17dBm | | 69 | 100 | mA |
| | Bypass Power Mode, Pout=8dBm | | 14 | 20 | mA |
| Quiescent Current | High Power Mode | 75 | 100 | 125 | mA |
| | Mid Power Mode | 15 | 25 | 35 | mA |
| | Bypass Mode | 1.5 | 3 | 4.5 | mA |
| Enable Current | High Power Mode | | 10 | | μA |
| | Mid Power Mode | | 10 | | μA |
| | Bypass Mode | | 10 | | μA |
| Mode Control Current | Mid Power Mode | | 5 | | μA |
| | Bypass Mode | | 5 | | μA |
| Bypass Control Current | | | | 100 | uA |
| Total Current in Power-down mode | Ven_Hi=0V, Vmode=0V, Vbp=0V | | 0.2 | 5 | μA |
| Adjacent Channel Leakage Ratio | 5 MHz offset 10 MHz offset | High Power Mode, Pout=27dBm | | -36 | dBc |
| | | | | -46 | dBc |
| | 5 MHz offset 10 MHz offset | High Power Mode, Pout=26dBm (HSDPA, HSUPA MPR=0dB) | | -35 | dBc |
| | | | | -46 | dBc |
| | 5 MHz offset 10 MHz offset | Mid Power Mode, Pout=17dBm | | -36 | dBc |
| | | | | -46 | dBc |
| | 5 MHz offset 10 MHz offset | Mid Power Mode, Pout=16dBm (HSDPA, HSUPA MPR=0dB) | | -36 | dBc |
| | | | | -46 | dBc |
| 5 MHz offset 10 MHz offset | Bypass Mode, Pout=8dBm | | -36 | dBc | |
| | | | -46 | dBc | |
| Harmonic Suppression | Second Third | High Power Mode, Pout=27dBm | | -30 | dBc |
| | | | | -40 | dBc |
| Input VSWR | | | 2:1 | 2.5:1 | |
| Stability (Spurious Output) | In-Band Load VSWR <= 5:1, All Phase Out of Band Load VSWR <= 10:1, All Phase Forwarded power fixed | | | -60 | dBc |
| Rx Band Noise Power | | | -140 | -136 | dBm/Hz |
| GPS Band Noise | | | -141 | -137 | dBm/Hz |
| ISM Band Noise | | | -144 | -140 | dBm/Hz |
| Phase Discontinuity | mid power mode ↔ high power mode, at Pout=17dBm | | 19 | | deg |
| | low power mode ↔ mid power mode, at Pout=8dBm | | 4 | | deg |
| Ruggedness | No Damage Pout<27dBm, Pin<10dBm, All phase High Power Mode | | | 10:1 | VSWR |

Electrical Characteristics in Band8

– Conditions: Vcc=3.4V, Ven_Low=2.6V, T=25°C, Zin/Zout=50ohm

– Signal Configuration: 3GPP (DPCCH+1DPDCH) Up-Link unless specified otherwise

| Characteristics | Condition | Min. | Typ. | Max. | Unit |
|----------------------------------|---|---|--------|-------|--------|
| Operating Frequency Range | | 890 | – | 915 | MHz |
| Gain | High Power Mode, Pout=27.5dBm | 24 | 27.2 | | dB |
| | Mid Power Mode, Pout=17dBm | 13.5 | 17.5 | | dB |
| | Bypass Power Mode, Pout=8dBm | 10 | 14.4 | | dB |
| Total Supply Current | High Power Mode, Pout=27.5dBm | | 429 | 485 | mA |
| | Mid Power Mode, Pout=17dBm | | 74 | 105 | mA |
| | Bypass Power Mode, Pout=8dBm | | 14 | 20 | mA |
| Quiescent Current | High Power Mode | 70 | 95 | 120 | mA |
| | Mid Power Mode | 10 | 21 | 30 | mA |
| | Bypass Mode | 2 | 3.5 | 5 | mA |
| Enable Current | High Power Mode | | 10 | | μA |
| | Mid Power Mode | | 10 | | μA |
| | Bypass Mode | | 10 | | μA |
| Mode Control Current | Mid Power Mode | | 5 | | μA |
| | Bypass Mode | | 5 | | μA |
| Bypass Control Current | | | | 100 | uA |
| Total Current in Power-down mode | Ven_Low=0V, Vmode=0V, Vbp=0V | | 0.2 | 5 | μA |
| Adjacent Channel Leakage Ratio | 5 MHz offset 10 MHz offset | High Power Mode, Pout=27.5dBm | | -36 | dBc |
| | | | | -46 | dBc |
| | 5 MHz offset 10 MHz offset | High Power Mode, Pout=26.5dBm (HSDPA, HSUPA MPR=0dB) | | -35 | dBc |
| | | | | -46 | dBc |
| | 5 MHz offset 10 MHz offset | Mid Power Mode, Pout=17dBm | | -36 | dBc |
| | | | | -46 | dBc |
| | 5 MHz offset 10 MHz offset | Mid Power Mode, Pout=16dBm (HSDPA, HSUPA MPR=0dB) | | -36 | dBc |
| | | | -46 | dBc | |
| 5 MHz offset 10 MHz offset | Bypass Mode, Pout=8dBm | | -36 | dBc | |
| | | | -46 | dBc | |
| 5 MHz offset 10 MHz offset | Bypass Mode, Pout=7dBm (HSDPA, HSUPA MPR=0dB) | | -36 | dBc | |
| | | | -46 | dBc | |
| Harmonic Suppression | Second | High Power Mode, Pout=27.5 dBm | | -30 | dBc |
| | Third | | | -40 | dBc |
| Input VSWR | | | 2:1 | 2.5:1 | |
| Stability (Spurious Output) | In-Band Load VSWR <= 5:1, All Phase Out of Band Load VSWR <= 10:1, All Phase Forwarded power fixed | | | -60 | dBc |
| Rx Band Noise Power | | | -135.5 | -133 | dBm/Hz |
| GPS Band Noise | | | -150 | -145 | dBm/Hz |
| ISM Band Noise | | | -160 | -155 | dBm/Hz |
| Phase Discontinuity | mid power mode ↔ high power mode, at Pout=17dBm | | 6 | | deg |
| | low power mode ↔ mid power mode, at Pout=8dBm | | 25 | | deg |
| Ruggedness | No Damage Pout<27.5dBm, Pin<10dBm, All phase High Power Mode | | | 10:1 | VSWR |

HSDPA Signal configuration used:

3GPP TS 34.121-1

Annex C (normative e): Measurement channels

C.10.1 UL reference measurement channel for HSDPA tests

Table C.10.1.4: β values for transmitter characteristics tests with HS-DPCCH

Sub-test 2 (CM=1.0, MPR=0.0)

HSUPA signal configuration used:

3GPP TS 34.121-1

Annex C (normative): Measurement channels

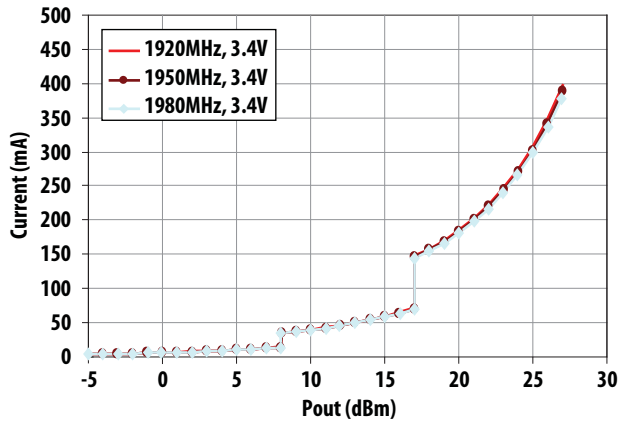
C.11.1 UL reference measurement channel for E-DCH tests

Table C.11.1.3: β values for transmitter characteristics tests with HS-DPCCH and E-DCH

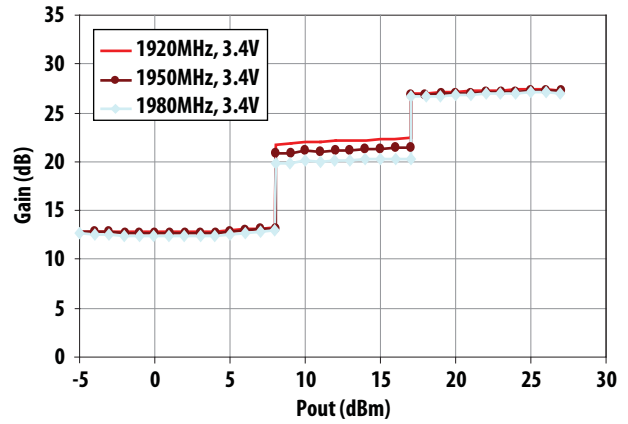
Sub-test 1 (CM=1.0, MPR=0.0)

Characteristics Data of Band1

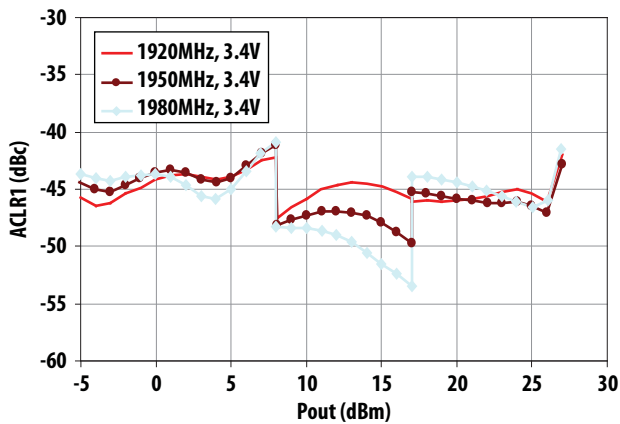
(Vcc=3.4V, Ven_Hi=2.6, Vbp, Vmode= 0V or 2.6V, T=25°C, Zin/Zout=50ohm, Rel99)



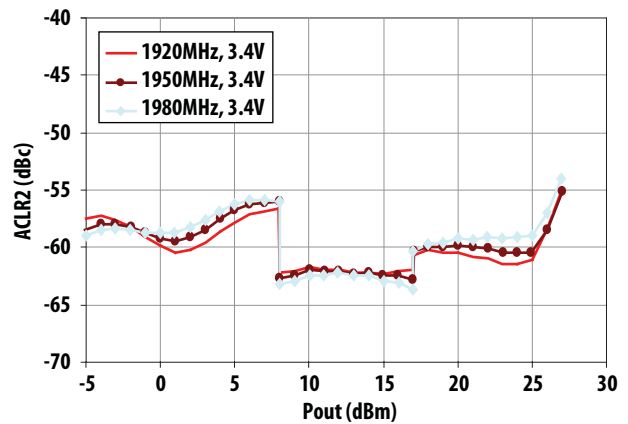
Total Current vs. Output Power



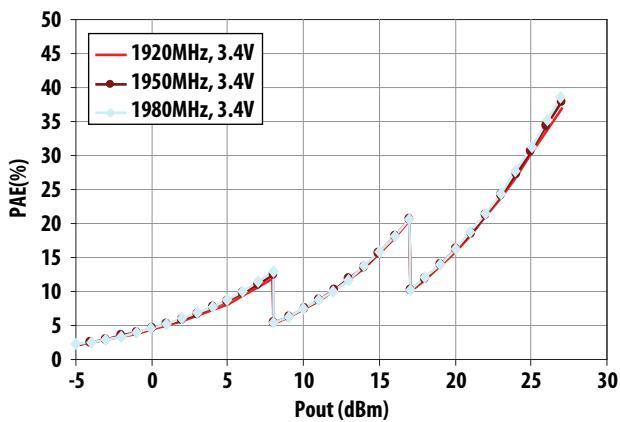
Gain vs. Output Power



Adjacent Channel Leakage Ratio 1 vs. Output Power



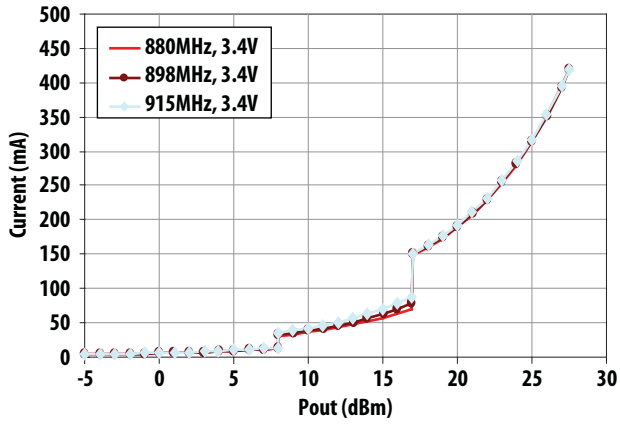
Adjacent Channel Leakage Ratio 2 vs. Output Power



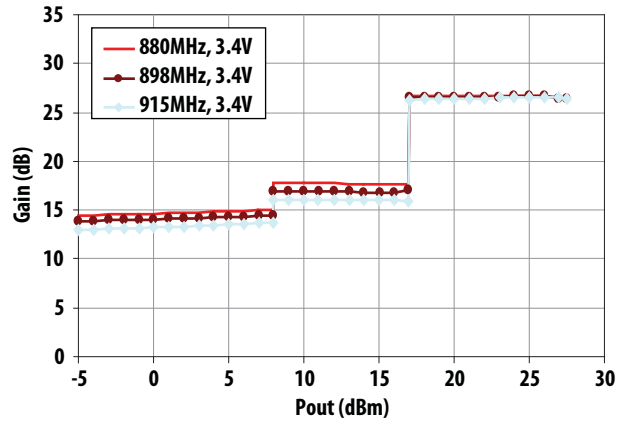
Power Added Efficiency vs. Output Power

Characteristics Data of Band8

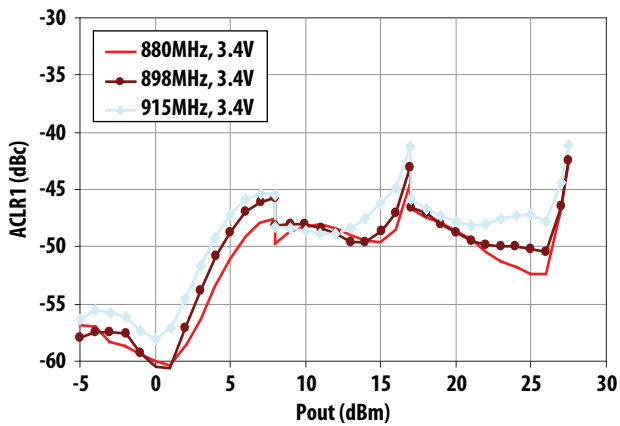
(Vcc=3.4V, Ven_Low=2.6, Vbp and Vmode= 0V or 2.6V, T=25°C, Zin/Zout=50ohm, Rel99)



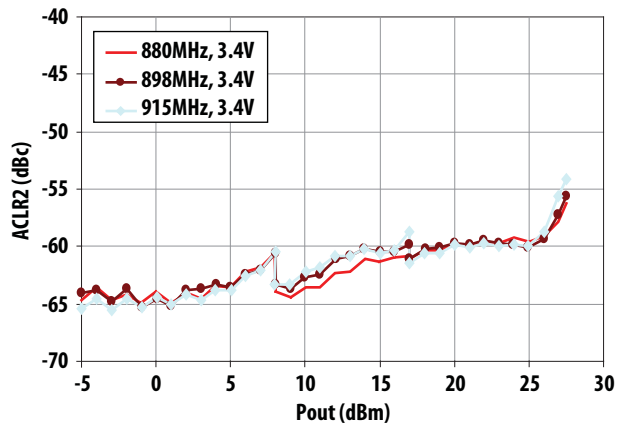
Total Current vs. Output Power



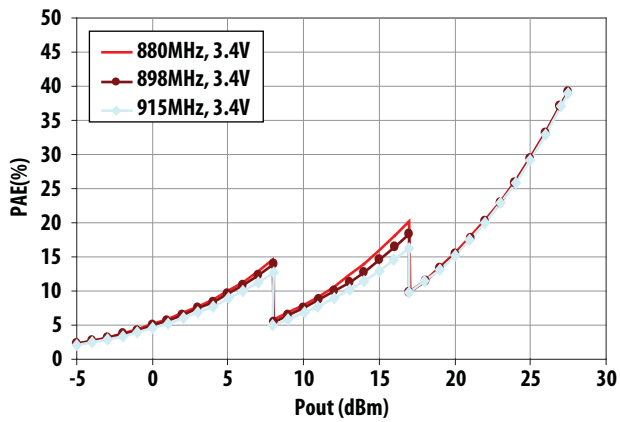
Gain vs. Output Power



Adjacent Channel Power Ratio 1 vs. Output Power



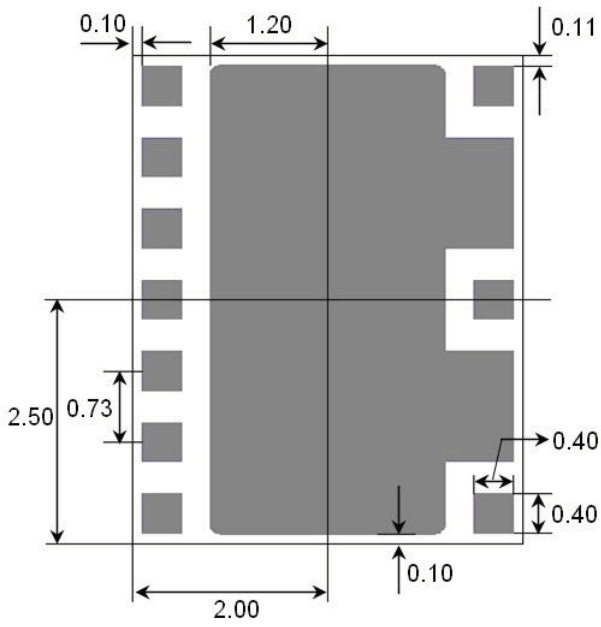
Adjacent Channel Power Ratio 2 vs. Output Power



Power Added Efficiency vs. Output Power

Footprint

All dimensions are in millimeter



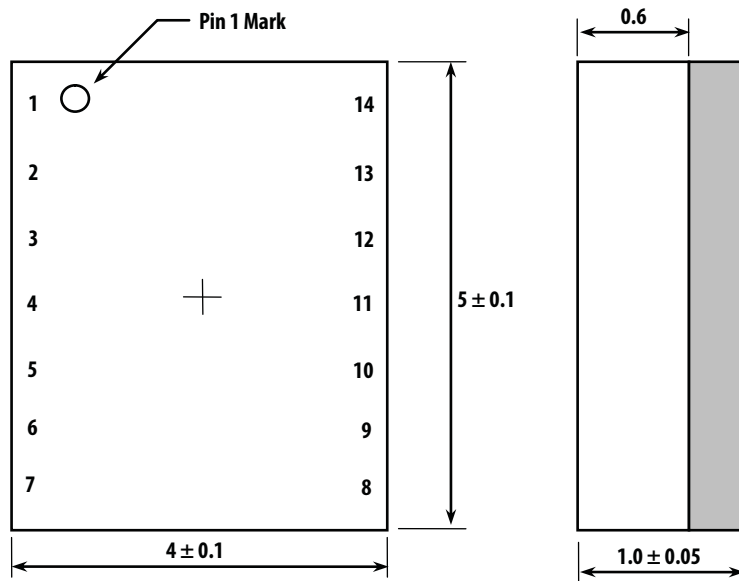
X-RAY TOP VIEW

PIN DESCRIPTIONS

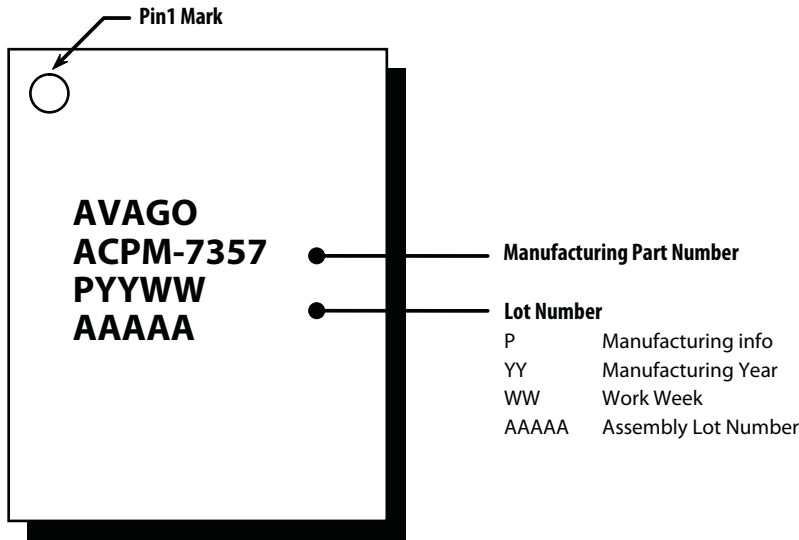
| Pin # | Name | Description |
|-------|-----------|-----------------|
| 1 | RFIn_Low | Band8 RF Input |
| 2 | Vmode | Mode Control |
| 3 | Vbp | Bypass Control |
| 4 | Vcc1 | Supply Voltage |
| 5 | Ven_Low | Band8 PA Enable |
| 6 | Ven_Hi | Band1 PA Enable |
| 7 | RFIn_Hi | Band1 RF Input |
| 8 | RFOut_Hi | Band1 RF Output |
| 9 | GND | Ground |
| 10 | GND | Ground |
| 11 | Vcc2 | Supply Voltage |
| 12 | GND | Ground |
| 13 | GND | Ground |
| 14 | RFOut_Low | Band8 RF Output |

Package Dimensions

All dimensions are in millimeter



Marking Specification



CoolPAM

Avago Technologies' CoolPAM is stage-bypass PA technology which saves more power compared with conventional PA. With this technology, the ACPM-7357 has very low quiescent current, and efficiencies at low and medium output power ranges are high.

Incorporation of bias circuit

The ACPM-7357 has internal bias circuit, which removes the need for external constant voltage source (LDO). PA on/off is controlled by Ven. This is digitally control pin.

3-mode power control with two mode control pins

The ACPM-7357 supports three power modes (bypass power mode/mid power mode/high power mode) with two mode control pins (Vmode and Vbp). This control scheme enables the ACPM-7357 to save power consumption more, which accordingly gives extended talk time.

PDF (probability density function) in the Figure 1. showing distribution of output power of mobile in real field gives motivation for stage-bypass PA. Output power is less than 16dBm for most of operating time (during talking), so it is important to save power consumption at low and medium output power ranges.

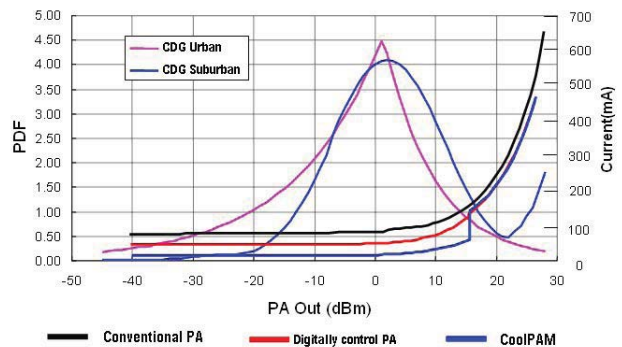


Figure 1. PDF and Current

Average current & Talk time

Average current consumed by PA can be calculated by summing up current at each output power weighted with probability. So it is expressed with integration of multiplication of current and probability at each output power.

$$\text{Average current} = \int (\text{PDF} \times \text{Current}) dp$$

Talk time is extended more as average current consumption is lowered.

Mode control pins

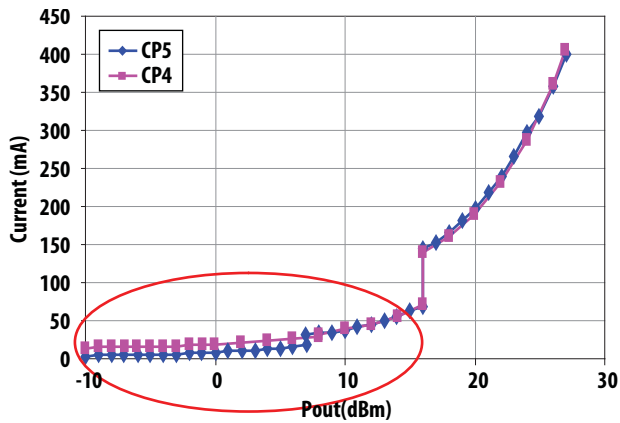
Vmode and Vbp are digitally controlled by baseband and they control the operating mode of the PA. The logic table is summarized in the below table. These pins do not require constant voltage for interface.

| Power Mode | Ven_Low, Ven_Hi | Vbp | Vmode | Pout (Rel99) | Pout (HSDPA, HSUPA MPR=0dB) |
|-----------------|--------------------|------|-------|-------------------------------------|---------------------------------------|
| High Power Mode | HIGH | LOW | LOW | ~27.0dBm (Band1) ~27.5dBm(Band8) | ~26.0dBm (Band1) ~ 26.5dBm (Band8) |
| Mid Power Mode | HIGH | LOW | HIGH | ~17dBm | ~16dBm |
| Bypass Mode | HIGH | HIGH | HIGH | ~8dBm | ~7dBm |
| Shut Down Mode | LOW | LOW | LOW | - | - |

Operating logic table.

UMTS PA performance comparison

- CoolPAM 4 and CoolPAM 5



The 5th generation of CoolPAM technology, ACPM-7357 can dramatically reduce Icc down to 3mA at bypass mode, which improves overall talk time and battery usage time of handset more compared with the CP4.

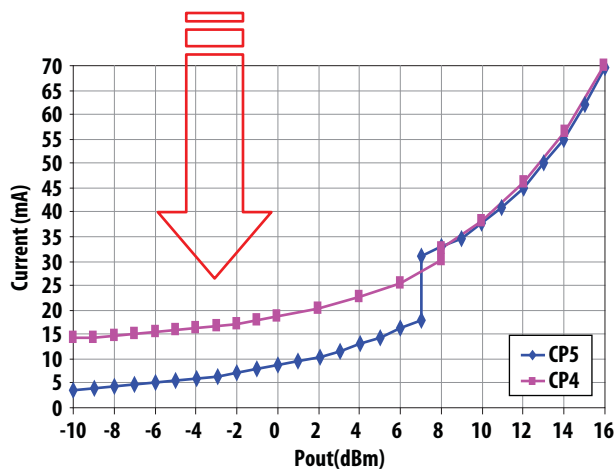


Figure 2. Icc Comparison of CP5 to CP4 (Avago CoolPAM)

Application on mobile phone board

The figure 3 shows an application example in mobile. C5 and C6 should be placed close to pin4 and pin11. Bypass cap C1, C2, C3 and C4 should be also placed nearby from pin2, pin3, pin5 and pin6, respectively. The length of post-PA transmission line should be minimized to reduce line loss.

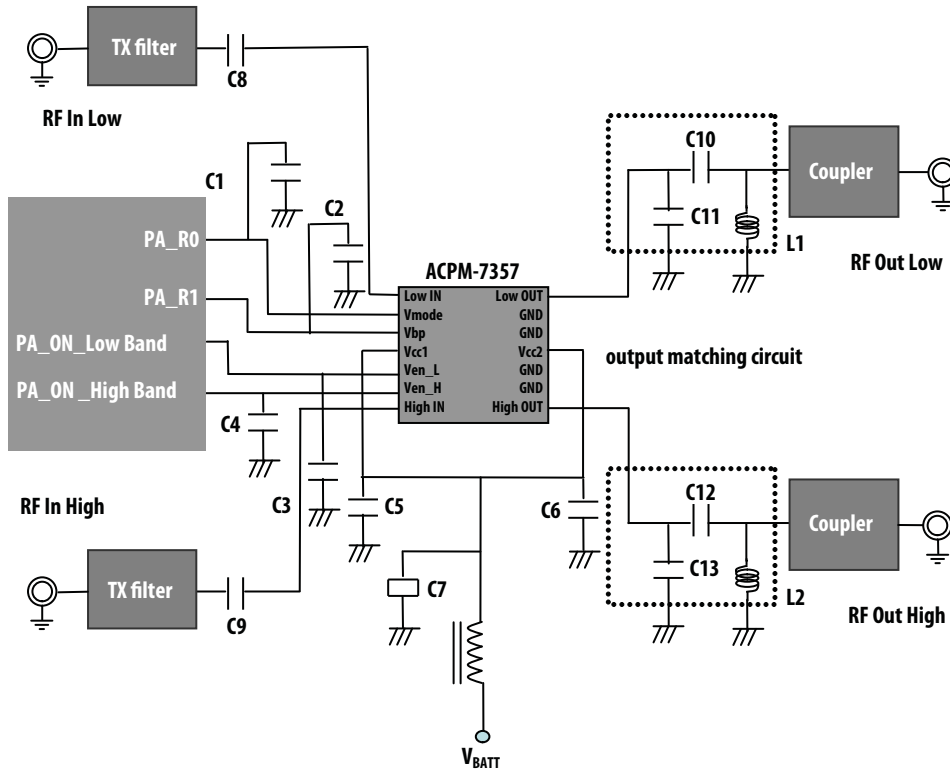


Figure 3. Peripheral Circuits

PCB layout and part placement on phone board

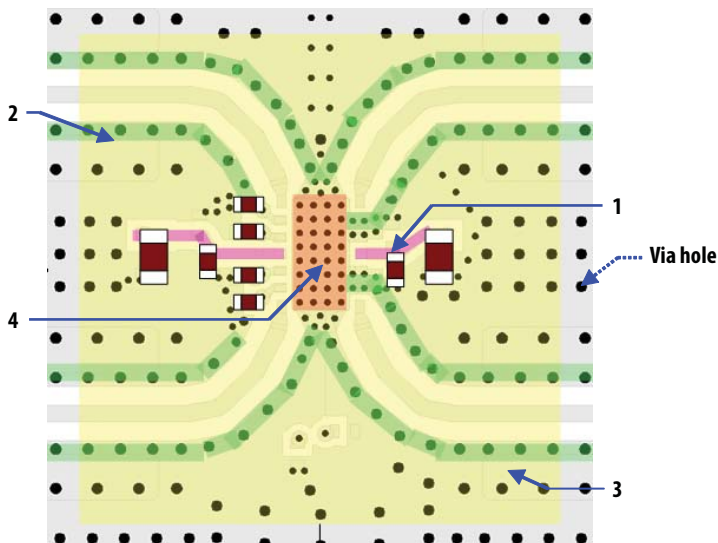
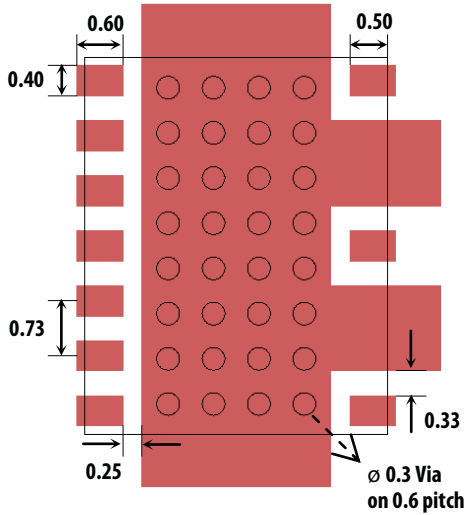


Figure 4. PCB guideline on phone board

Notes:

1. To prevent voltage drop, make the bias lines as wide as possible (Pink line).
2. Use many via holes to fence off PA RF input and output traces for better isolation. Output signal of the PA should be isolated from input signal and the receive signal. Output signal should not be fed into PA input. (Green line)
3. Use via holes to connect outer ground plates to internal ground planes. They help heat spread out more easily and accordingly the board temperature can be lowered. They also help to improve RF stability (Yellow square).
4. PA which has a ground slug requires many via holes which go through all the layers (Red square).

Metallization



PCB Design Guidelines

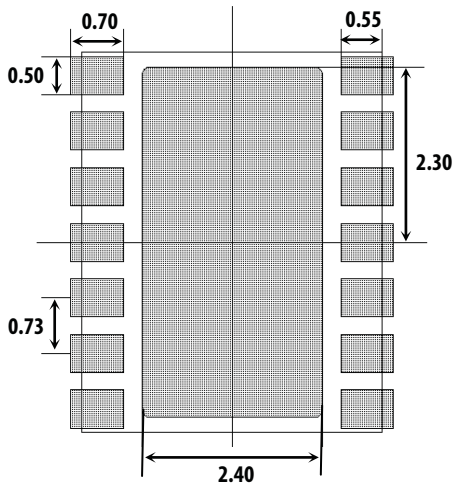
The recommended PCB land pattern is shown in figures on the left side. The substrate is coated with solder mask between the I/O and conductive paddle to protect the gold pads from short circuit that is caused by solder bleeding/bridging.

Stencil Design Guidelines

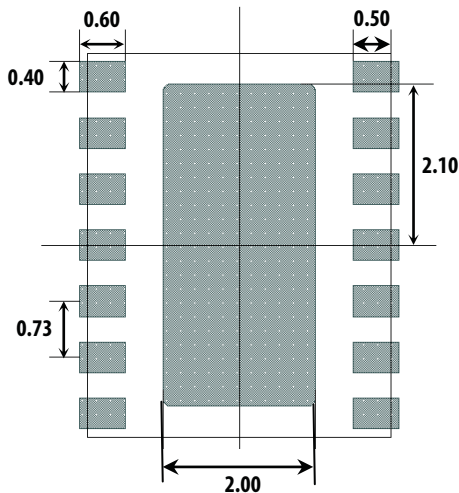
A properly designed solder screen or stencil is required to ensure optimum amount of solder paste is deposited onto the PCB pads.

The recommended stencil layout is shown here. Reducing the stencil opening can potentially generate more voids. On the other hand, stencil openings larger than 100% will lead to excessive solder paste smear or bridging across the I/O pads or conductive paddle to adjacent I/O pads. Considering the fact that solder paste thickness will directly affect the quality of the solder joint, a good choice is to use laser cut stencil composed of 0.100mm(4mils) or 0.127mm(5mils) thick stainless steel which is capable of producing the required fine stencil outline.

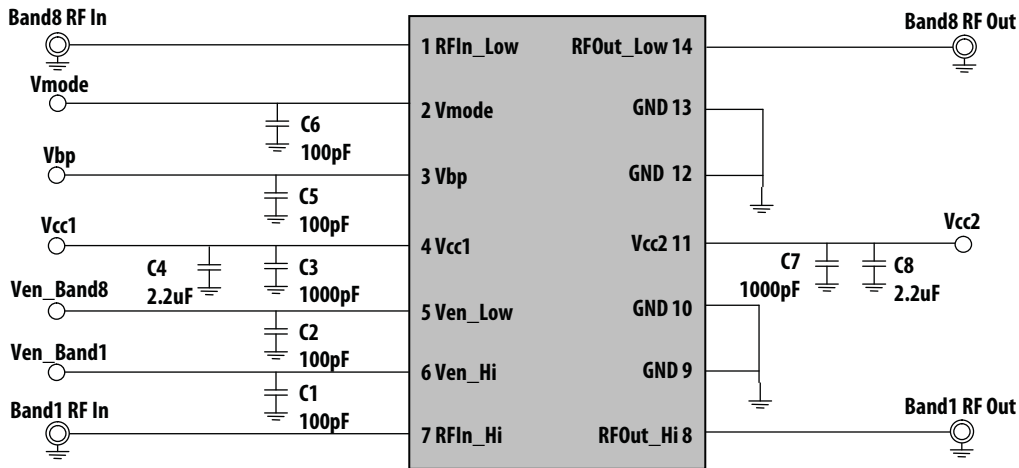
Solder Mask Opening



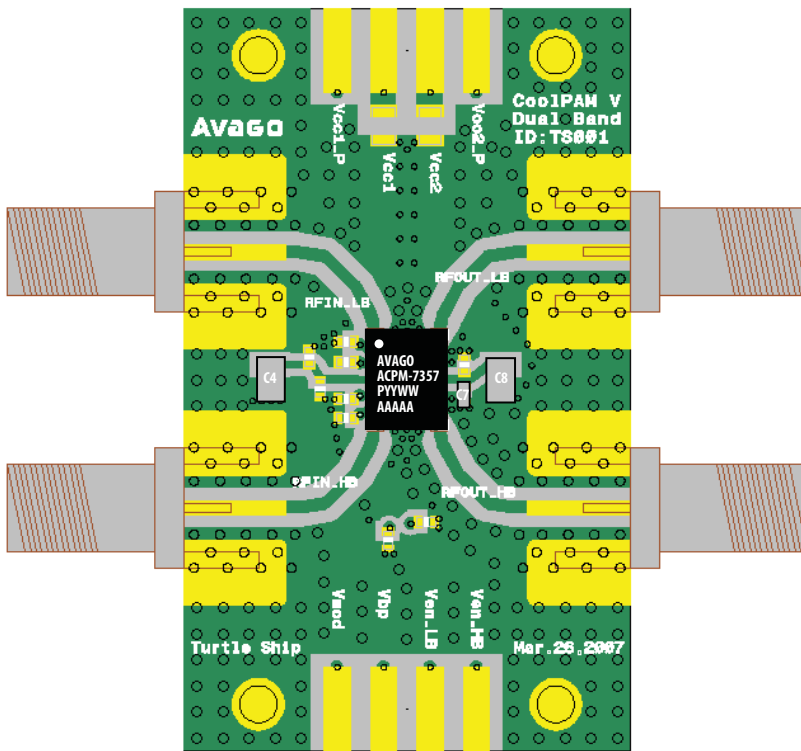
Solder Paste Stencil Aperture



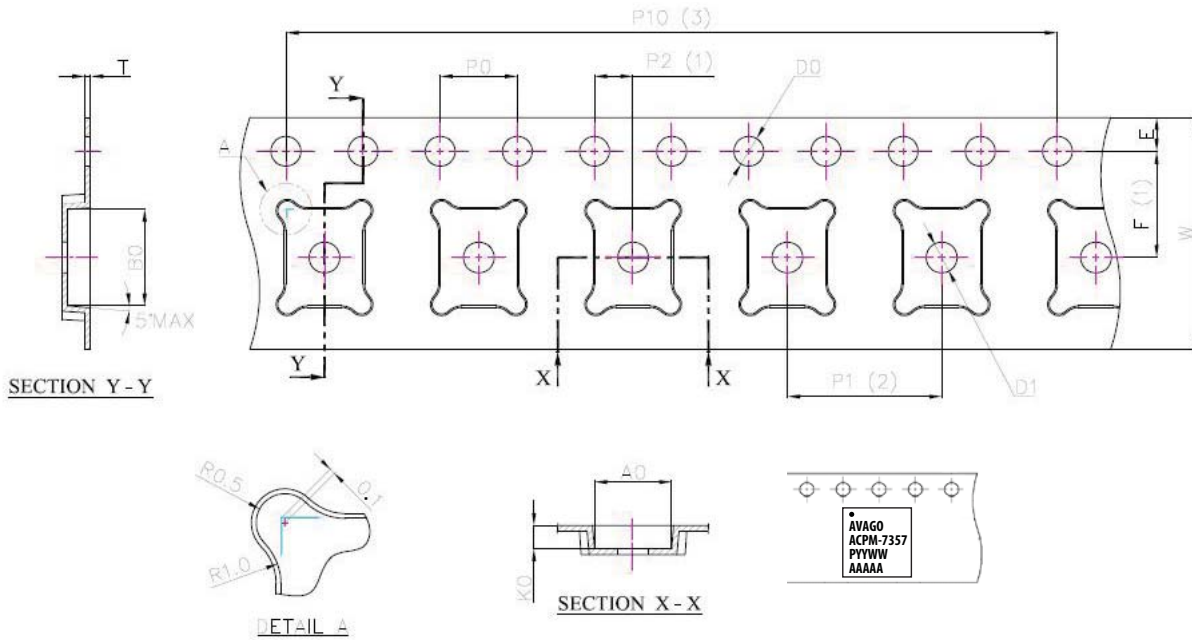
Evaluation Board Schematic



Evaluation Board Description



Tape and Reel Information



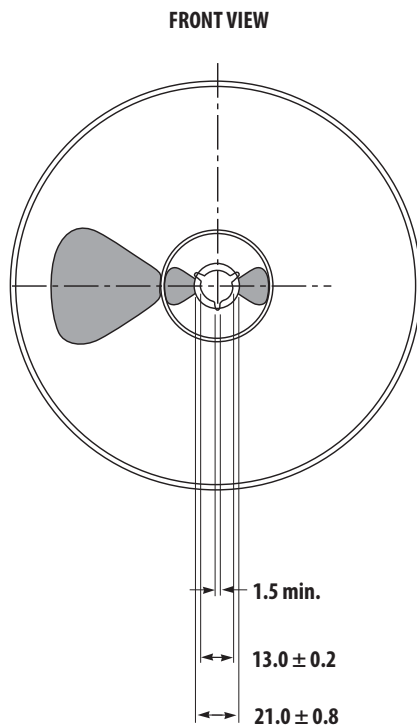
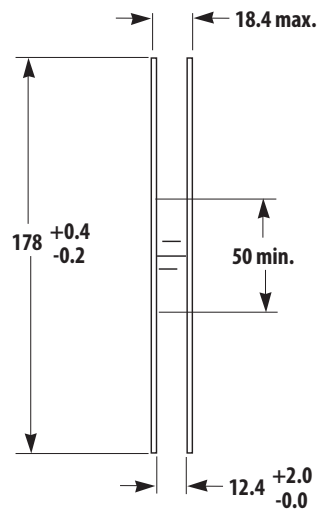
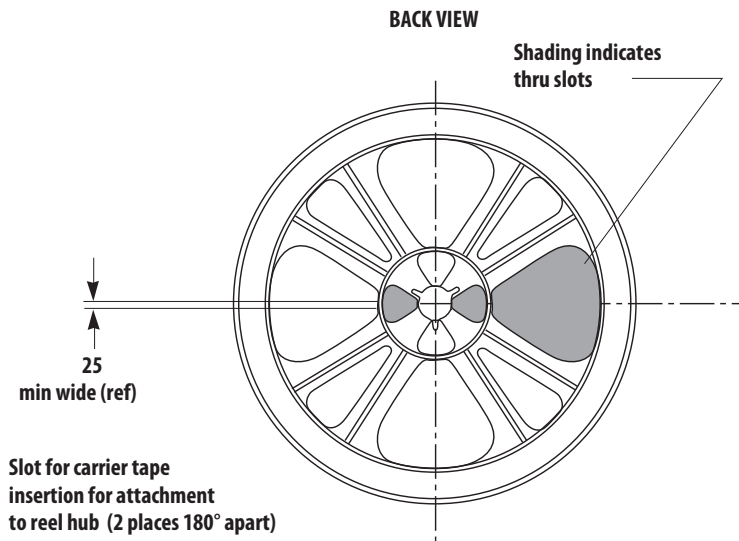
Dimension List

| Dimension | Millimeter |
|-----------|------------|
| A0 | 4.40±0.10 |
| B0 | 5.30±0.10 |
| K0 | 1.20±0.10 |
| D0 | 1.55±0.05 |
| D1 | 1.60±0.10 |
| P0 | 4.00±0.10 |
| P1 | 8.00±0.10 |

| Dimension | Millimeter |
|-----------|------------|
| P2 | 2.00±0.05 |
| P10 | 40.00±0.20 |
| E | 1.75±0.10 |
| F | 5.50±0.05 |
| W | 12.00±0.30 |
| T | 0.30±0.05 |

Tape and Reel Format – 4 mm x 5 mm

Reel Drawing



NOTES:

1. Reel shall be labeled with the following information (as a minimum).
 - a. manufacturers name or symbol
 - b. Avago Technologies part number
 - c. purchase order number
 - d. date code
 - e. quantity of units
2. A certificate of compliance (c of c) shall be issued and accompany each shipment of product.
3. Reel must not be made with or contain ozone depleting materials.
4. All dimensions in millimeters (mm)

Plastic Reel Format (all dimensions are in millimeters)

Handling and Storage

ESD (Electrostatic Discharge)

Electrostatic discharge occurs **naturally in the environment**. With the increase in voltage potential, the outlet of neutralization or discharge will be sought. If the acquired discharge route is **through a semiconductor device**, destructive damage will result.

ESD countermeasure methods should be developed and used to control potential ESD damage during handling in a factory environment at each manufacturing site.

MSL (Moisture Sensitivity Level)

Plastic encapsulated surface mount package is sensitive to damage induced by absorbed moisture and temperature.

Avago Technologies follows JEDEC Standard J-STD 020B. Each component and package type is classified for moisture sensitivity by soaking a known dry package at

various temperatures and relative humidity, and times. After soak, the components are **subjected to three consecutive simulated reflows**.

The out of bag exposure time maximum limits are determined by the classification test describe below which corresponds to a MSL classification level 6 to 1 according to the JEDEC standard IPC/JEDEC J-STD-020B and J-STD-033.

ACPM-7357 is MSL3. Thus, according to the J-STD-033 p.10, the maximum Manufacturers Exposure Time (MET) for this part is 168 hours. After this time period, the part would need to be removed from the reel, de-taped and then re-baked. MSL classification reflow temperature for the ACPM-7357 is targeted at 260°C +0/-5°C. Figure and table on next page show typical SMT profile for maximum temperature of 260 +0/-5°C.

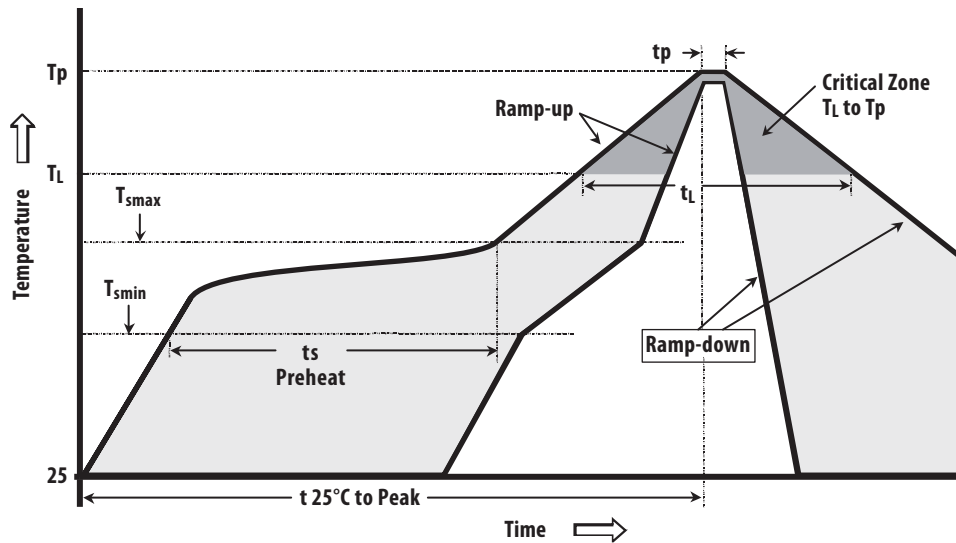
Moisture Classification Level and Floor Life

| MSL Level | Floor Life (out of bag) at factory ambient =< 30°C/60% RH or as stated |
|-----------|--|
| 1 | Unlimited at =< 30°C/85% RH |
| 2 | 1 year |
| 2a | 4 weeks |
| 3 | 168 hours |
| 4 | 72 hours |
| 5 | 48 hours |
| 5a | 24 hours |
| 6 | Mandatory bake before use. After bake, must be reflowed within the time limit specified on the label |

Note :

1. The MSL Level is marked on the MSL Label on each shipping bag.

Reflow Profile Recommendations



Typical SMT Reflow Profile for Maximum Temperature = $260 \pm 5^\circ\text{C}$

Typical SMT Reflow Profile for Maximum Temperature = $260 \pm 5^\circ\text{C}$

| Profile Feature | Sn-Pb Solder | Pb-Free Solder |
|--|---------------------------|---------------------------|
| Average ramp-up rate (TL to TP) | 3°C/sec max | 3°C/sec max |
| Preheat | | |
| – Temperature Min (T _{smin}) | 100°C | 150°C |
| – Temperature Max (T _{smax}) | 150°C | 200°C |
| – Time (min to max) (t _s) | 60-120 sec | 60-120 sec |
| T _{smax} to T _L | | |
| – Ramp-up Rate | | 3°C/sec max |
| Time maintained above: | | |
| – Temperature (T _L) | 183°C | 217°C |
| – Time (T _L) | 60-150 sec | 60-150 sec |
| Peak temperature (T _p) | 240 $\pm 5^\circ\text{C}$ | 260 $\pm 5^\circ\text{C}$ |
| Time within 5°C of actual Peak Temperature (t _p) | 10-30 sec | 20-40 sec |
| Ramp-down Rate | 6°C/sec max | 6°C/sec max |
| Time 25°C to Peak Temperature | 6 min max. | 8 min max. |

Storage Condition

Packages described in this document must be stored in sealed moisture barrier, antistatic bags. Shelf life in a sealed moisture barrier bag is 12 months at <40°C and 90% relative humidity (RH) J-STD-033 p.6.

Out-of-Bag Time Duration

After unpacking the device must be soldered to the PCB within 168 hours with factory conditions <30°C and 60% RH as listed in the Table 5-1 on the J-STD-020D p.6.

Baking

It is not necessary to re-bake the part if both conditions (storage conditions and out-of-bag conditions) have been satisfied. **Baking must be done if at least one of the conditions above has not been satisfied.** The baking conditions are listed in the Table 4-1 on the J-STD-033 p.8.

CAUTION

Tape and reel materials typically cannot be baked at the temperature described above. If out-of-bag exposure time is exceeded, parts must be baked for a longer time at low temperatures, or the parts must be de-reeled, de-taped, re-baked and then put back on tape and reel. (See moisture sensitive warning label on each shipping bag for information of baking).

Board Rework

Component Removal, Rework and Remount

If a component is to be removed from the board, it is recommended that localized heating be used and the maximum body temperatures of any surface mount component on the board not exceed 200°C. This method will minimize moisture related component damage. If any component temperature exceeds 200°C, the board must be baked dry per 4-2 prior to rework and/or component removal. Component temperatures shall be measured at the top center of the package body. Any SMD packages that have not exceeded their floor life can be exposed to a maximum body temperature as high as their specified maximum reflow temperature.

Removal for Failure Analysis

Not following the above requirements may cause moisture/reflow damage that could hinder or completely prevent the determination of the original failure mechanism.

Baking of Populated Boards

Some SMD packages and board materials are not able to withstand long duration bakes at 125°C. Examples of this are some FR-4 materials, which cannot withstand a 24 hr bake at 125°C. Batteries and electrolytic capacitors are also temperature sensitive. With component and board temperature restrictions in mind, **choose a bake temperature from Table 4-1 in J-STD 033;** then determine the appropriate bake duration based on the component to be removed. For additional considerations see IPC-7711 and IPC-7721.

Derating due to Factory Environmental Conditions

Factory floor life exposures for SMD packages removed from the dry bags will be a function of the ambient environmental conditions. A safe, yet conservative, handling approach is to expose the SMD packages only up to the maximum time limits for each moisture sensitivity level as shown in table of Moisture Classification Level and Floor Life. This approach, however, does not work if the factory humidity or temperature is greater than the testing conditions of 30°C/60% RH. A solution for addressing this problem is to derate the exposure times based on the knowledge of moisture diffusion in the component package materials ref. JESD22-A120). Recommended equivalent total floor life exposures can be estimated for a range of humidities and temperatures based on the nominal plastic thickness for each device.

Table on following page lists equivalent derated floor lives for humidities ranging from 20-90% RH for three temperature, 20°C, 25°C, and 30°C.

This table is applicable to SMDs molded with novolac, biphenyl or multifunctional epoxy mold compounds. The following assumptions were used in calculating this table:

1. Activation Energy for diffusion = 0.35eV (smallest known value).
2. For ≤60% RH, use Diffusivity = $0.121 \exp(-0.35\text{eV}/kT)$ mm²/s (this used smallest known Diffusivity @ 30°C).
3. For >60% RH, use Diffusivity = $1.320 \exp(-0.35\text{eV}/kT)$ mm²/s (this used largest known Diffusivity @ 30°C).

Recommended Equivalent Total Floor Life (days) @ 20°C, 25°C & 30°C, 35°C

For ICs with Novolac, Biphenyl and Multifunctional Epoxies (Reflow at same temperature at which the component was classified) Maximum Percent Relative Humidity

| Maximum Percent Relative Humidity | | | | | | | | | | | | | |
|---|----------------------------|----|-----|-----|-----|-----|-----|-----|-----|-----|------|------|------|
| Package Type and Body Thickness | Moisture Sensitivity Level | 5% | 10% | 20% | 30% | 40% | 50% | 60% | 70% | 80% | 90% | | |
| Body Thickness ≥3.1 mm Including PQFPs >84 pin, PLCCs (square) All MQFPs or All BGAs ≥1 mm | Level 2a | ∞ | ∞ | 94 | 44 | 32 | 26 | 16 | 7 | 5 | 4 | 35°C | |
| | | ∞ | ∞ | 124 | 60 | 41 | 33 | 28 | 10 | 7 | 6 | 30°C | |
| | | ∞ | ∞ | 167 | 78 | 53 | 42 | 36 | 14 | 10 | 8 | 25°C | |
| | | ∞ | ∞ | 231 | 103 | 69 | 57 | 47 | 19 | 13 | 10 | 20°C | |
| | Level 3 | ∞ | ∞ | 8 | 7 | 6 | 6 | 6 | 4 | 3 | 3 | 35°C | |
| | | ∞ | ∞ | 10 | 9 | 8 | 7 | 7 | 5 | 4 | 4 | 30°C | |
| | | ∞ | ∞ | 13 | 11 | 10 | 9 | 9 | 7 | 6 | 5 | 25°C | |
| | | ∞ | ∞ | 17 | 14 | 13 | 12 | 12 | 10 | 8 | 7 | 20°C | |
| | Level 4 | ∞ | 3 | 3 | 3 | 2 | 2 | 2 | 2 | 1 | 1 | 35°C | |
| | | ∞ | 5 | 4 | 4 | 4 | 3 | 3 | 3 | 2 | 2 | 30°C | |
| | | ∞ | 6 | 5 | 5 | 5 | 5 | 4 | 3 | 3 | 3 | 25°C | |
| | | ∞ | 8 | 7 | 7 | 7 | 7 | 6 | 5 | 4 | 4 | 20°C | |
| Level 5 | ∞ | 2 | 2 | 2 | 2 | 1 | 1 | 1 | 1 | 1 | 35°C | | |
| | ∞ | 4 | 3 | 3 | 2 | 2 | 2 | 2 | 1 | 1 | 30°C | | |
| | ∞ | 5 | 5 | 4 | 4 | 3 | 3 | 2 | 2 | 2 | 25°C | | |
| | ∞ | 7 | 7 | 6 | 5 | 5 | 4 | 3 | 3 | 3 | 20°C | | |
| Level 5a | ∞ | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 35°C | | |
| | ∞ | 2 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 30°C | | |
| | ∞ | 3 | 2 | 2 | 2 | 2 | 2 | 1 | 1 | 1 | 25°C | | |
| | ∞ | 5 | 4 | 3 | 3 | 3 | 2 | 2 | 2 | 2 | 20°C | | |
| Body 2.1 mm ≤ Thickness <3.1 mm including PLCCs (rectangular) 18-32 pin SOICs (wide body) SOICs ≥20 pins, PQFPs ≤80 pins | Level 2a | ∞ | ∞ | ∞ | ∞ | 58 | 30 | 22 | 3 | 2 | 1 | 35°C | |
| | | ∞ | ∞ | ∞ | ∞ | 86 | 39 | 28 | 4 | 3 | 2 | 30°C | |
| | | ∞ | ∞ | ∞ | ∞ | 148 | 51 | 37 | 6 | 4 | 3 | 25°C | |
| | | ∞ | ∞ | ∞ | ∞ | ∞ | 69 | 49 | 8 | 5 | 4 | 20°C | |
| | Level 3 | ∞ | ∞ | 12 | 9 | 7 | 6 | 5 | 2 | 2 | 1 | 35°C | |
| | | ∞ | ∞ | 19 | 12 | 9 | 8 | 7 | 3 | 2 | 2 | 30°C | |
| | | ∞ | ∞ | 25 | 15 | 12 | 10 | 9 | 5 | 3 | 3 | 25°C | |
| | | ∞ | ∞ | 32 | 19 | 15 | 13 | 12 | 7 | 5 | 4 | 20°C | |
| | Level 4 | ∞ | 5 | 4 | 3 | 3 | 2 | 2 | 1 | 1 | 1 | 35°C | |
| | | ∞ | 7 | 5 | 4 | 4 | 3 | 3 | 2 | 2 | 1 | 30°C | |
| | | ∞ | 9 | 7 | 5 | 5 | 4 | 4 | 3 | 2 | 2 | 25°C | |
| | | ∞ | 11 | 9 | 7 | 6 | 6 | 5 | 4 | 3 | 3 | 20°C | |
| Level 5 | ∞ | 3 | 2 | 2 | 2 | 2 | 1 | 1 | 1 | 1 | 35°C | | |
| | ∞ | 4 | 3 | 3 | 2 | 2 | 2 | 1 | 1 | 1 | 30°C | | |
| | ∞ | 5 | 4 | 3 | 3 | 3 | 3 | 2 | 1 | 1 | 25°C | | |
| | ∞ | 6 | 5 | 5 | 4 | 4 | 4 | 3 | 3 | 2 | 20°C | | |
| Level 5a | ∞ | 1 | 1 | 1 | 1 | 1 | 1 | 1 | 0.5 | 0.5 | 35°C | | |
| | ∞ | 2 | 1 | 1 | 1 | 1 | 1 | 1 | 0.5 | 0.5 | 30°C | | |
| | ∞ | 2 | 2 | 2 | 2 | 2 | 2 | 1 | 1 | 1 | 25°C | | |
| | ∞ | 3 | 2 | 2 | 2 | 2 | 2 | 2 | 2 | 1 | 20°C | | |
| Body Thickness <2.1 mm including SOICs <18 pin All TQFPs, TSOPs or All BGAs <1 mm body thickness | Level 2a | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | 17 | 1 | 0.5 | 0.5 | 35°C | |
| | | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | 28 | 1 | 1 | 1 | 30°C |
| | | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | 2 | 1 | 1 | 25°C |
| | | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | ∞ | 2 | 2 | 1 | 20°C |
| | Level 3 | ∞ | ∞ | ∞ | ∞ | ∞ | 8 | 5 | 1 | 0.5 | 0.5 | 35°C | |
| | | ∞ | ∞ | ∞ | ∞ | ∞ | 11 | 7 | 1 | 1 | 1 | 30°C | |
| | | ∞ | ∞ | ∞ | ∞ | ∞ | 14 | 10 | 2 | 1 | 1 | 25°C | |
| | | ∞ | ∞ | ∞ | ∞ | ∞ | 20 | 13 | 2 | 2 | 1 | 20°C | |
| | Level 4 | ∞ | ∞ | ∞ | 7 | 4 | 3 | 2 | 1 | 0.5 | 0.5 | 35°C | |
| | | ∞ | ∞ | ∞ | 9 | 5 | 4 | 3 | 1 | 1 | 1 | 30°C | |
| | | ∞ | ∞ | ∞ | 12 | 7 | 5 | 4 | 2 | 1 | 1 | 25°C | |
| | | ∞ | ∞ | ∞ | 17 | 9 | 7 | 6 | 2 | 2 | 1 | 20°C | |
| Level 5 | ∞ | ∞ | 7 | 3 | 2 | 2 | 1 | 1 | 0.5 | 0.5 | 35°C | | |
| | ∞ | ∞ | 13 | 5 | 3 | 2 | 2 | 1 | 1 | 1 | 30°C | | |
| | ∞ | ∞ | 18 | 6 | 4 | 3 | 3 | 2 | 1 | 1 | 25°C | | |
| | ∞ | ∞ | 26 | 8 | 6 | 5 | 4 | 2 | 2 | 1 | 20°C | | |
| Level 5a | ∞ | 7 | 2 | 1 | 1 | 1 | 1 | 1 | 0.5 | 0.5 | 35°C | | |
| | ∞ | 10 | 3 | 2 | 1 | 1 | 1 | 1 | 1 | 0.5 | 30°C | | |
| | ∞ | 13 | 5 | 3 | 2 | 2 | 2 | 1 | 1 | 1 | 25°C | | |
| | ∞ | 18 | 6 | 4 | 3 | 2 | 2 | 2 | 2 | 1 | 20°C | | |

For product information and a complete list of distributors, please go to our web site: www.avagotech.com

Avago, Avago Technologies, and the A logo are trademarks of Avago Technologies in the United States and other countries.
Data subject to change. Copyright © 2005-2009 Avago Technologies. All rights reserved.
AV02-2036EN - July 30, 2009

